

# Electronic Devices

## Final Term Lecture - 08

Reference book:

**Electronic Devices and Circuit Theory (Chapter-7)**

Robert L. Boylestad and L. Nashelsky , (11<sup>th</sup> Edition)



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# E-MOSFET VOLTAGE-DIVIDER BIAS

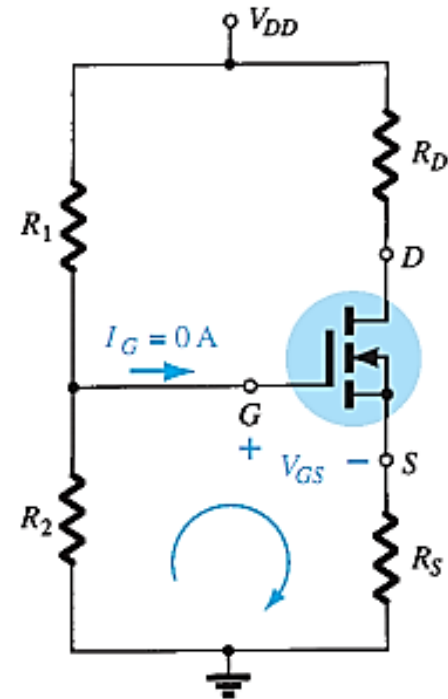
- E-MOSFETs use the **same procedure** to JFETs and D-MOSFETs.

$$V_G = \frac{R_2 V_{DD}}{R_1 + R_2}$$

$$V_{GS} = V_G - I_D R_S$$

$$V_{DS} = V_{DD} - I_D (R_D + R_S)$$

$$I_D = k(V_{GS} - V_T)^2$$



**FIG. 7.43**

*Voltage-divider biasing arrangement for an n-channel enhancement MOSFET.*

# E-MOSFET VOLTAGE-DIVIDER BIAS

- **Graphical Approach:**

- Calculate the value for

$$k = \frac{I_{D(on)}}{(V_{GS(on)} - V_{GS(Th)})^2}$$

- Plot  $V_{GS}$  vs  $I_D$  using

$$I_D = k(V_{GS} - V_T)^2$$

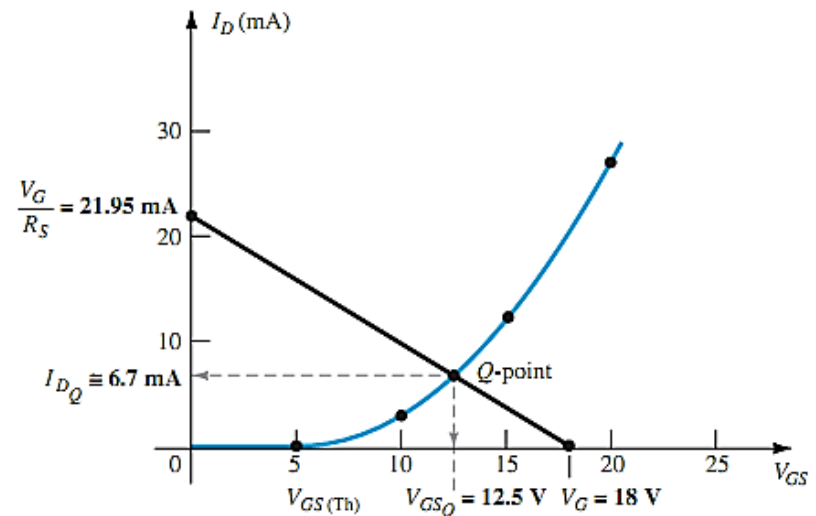
- Plot for:

»  $V_{GS} = V_G$  at  $I_D = 0A$

»  $V_{GS} = 0V$  at  $I_D = V_G/R_S$

$$V_{GS} = V_G - I_D R_S$$

- Identify the Q-point.



# E-MOSFET VOLTAGE-DIVIDER BIAS EXAMPLE

- Determine  $I_D$ ,  $V_{GS}$ , and  $V_{DS}$  for the following network:

$$V_G = \frac{R_2 V_{DD}}{R_1 + R_2} = \frac{(18 \text{ M}\Omega)(40 \text{ V})}{22 \text{ M}\Omega + 18 \text{ M}\Omega} = 18 \text{ V}$$

$$V_{GS} = V_G - I_D R_S = 18 \text{ V} - I_D(0.82 \text{ k}\Omega)$$

When  $I_D = 0 \text{ mA}$ ,

$$V_{GS} = 18 \text{ V} - (0 \text{ mA})(0.82 \text{ k}\Omega) = 18 \text{ V}$$

When  $I_D = 0 \text{ mA}$ ,

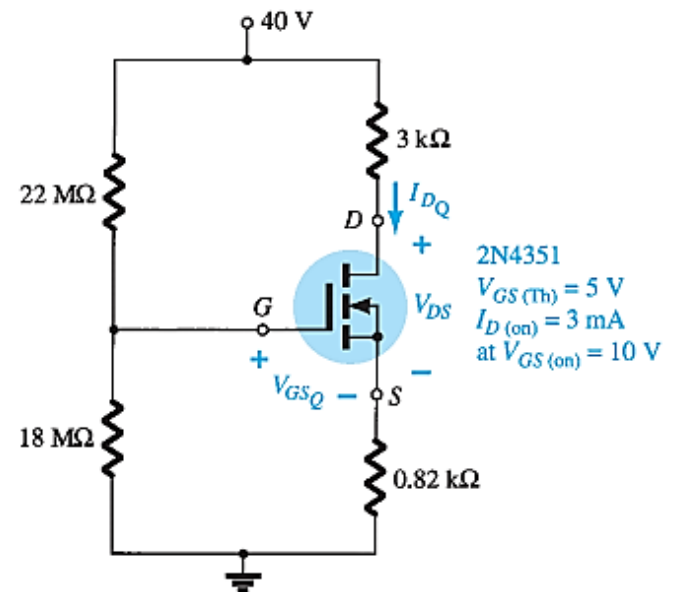
$$V_{GS} = 18 \text{ V} - (0 \text{ mA})(0.82 \text{ k}\Omega) = 18 \text{ V}$$

as appearing on Fig. 7.45. When  $V_{GS} = 0 \text{ V}$ ,

$$V_{GS} = 18 \text{ V} - I_D(0.82 \text{ k}\Omega)$$

$$0 = 18 \text{ V} - I_D(0.82 \text{ k}\Omega)$$

$$I_D = \frac{18 \text{ V}}{0.82 \text{ k}\Omega} = 21.95 \text{ mA}$$



**FIG. 7.44**

Example 7.11.

# E-MOSFET VOLTAGE-DIVIDER BIAS EXAMPLE

## Device

$$V_{GS(Th)} = 5 \text{ V}, \quad I_{D(on)} = 3 \text{ mA with } V_{GS(on)} = 10 \text{ V}$$

$$\begin{aligned} \text{Eq. (7.34): } k &= \frac{I_{D(on)}}{(V_{GS(on)} - V_{GS(Th)})^2} \\ &= \frac{3 \text{ mA}}{(10 \text{ V} - 5 \text{ V})^2} = 0.12 \times 10^{-3} \text{ A/V}^2 \end{aligned}$$

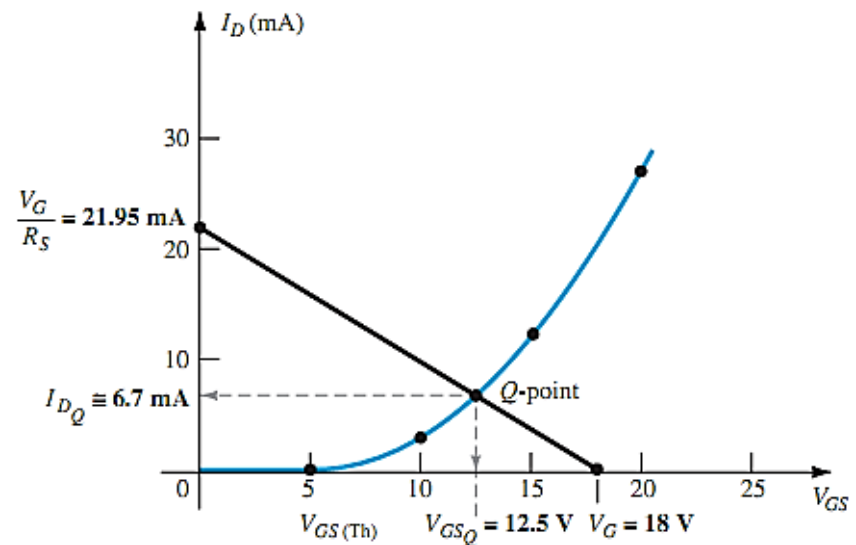
and

$$\begin{aligned} I_D &= k(V_{GS} - V_{GS(Th)})^2 \\ &= 0.12 \times 10^{-3}(V_{GS} - 5)^2 \end{aligned}$$

$$I_{DQ} \cong 6.7 \text{ mA}$$

$$V_{GSQ} = 12.5 \text{ V}$$

$$\begin{aligned} V_{DS} &= V_{DD} - I_D(R_S + R_D) \\ &= 40 \text{ V} - (6.7 \text{ mA})(0.82 \text{ k}\Omega + 3.0 \text{ k}\Omega) \\ &= 40 \text{ V} - 25.6 \text{ V} \\ &= 14.4 \text{ V} \end{aligned}$$



**FIG. 7.45**

Determining the Q-point for the network of Example 7.11.

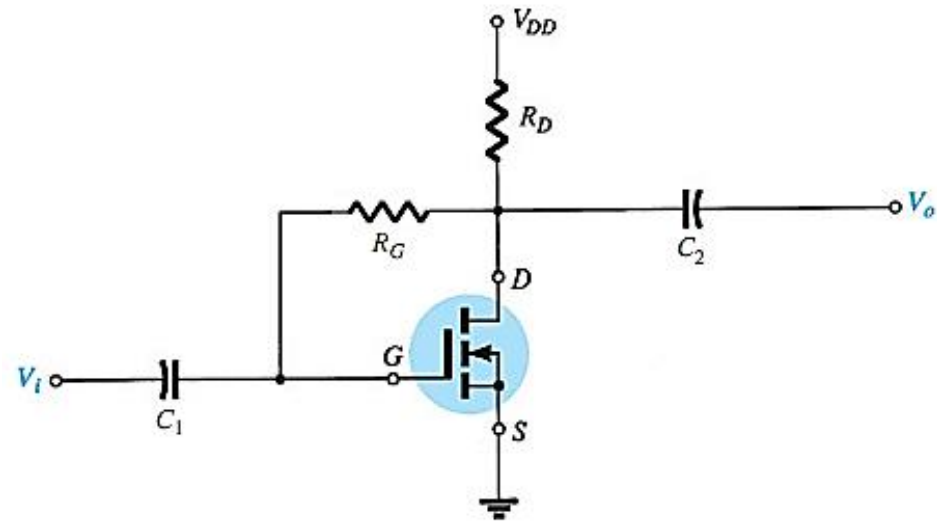
# E-MOSFET FEEDBACK BIAS

$$I_G \approx 0A$$

$$V_{RG} = 0V$$

$$V_{GS} = V_{DS}$$

$$V_{GS} = V_{DD} - I_D R_D$$



**FIG. 7.37**

*Feedback biasing arrangement.*

# E-MOSFET FEEDBACK BIAS

- **Graphical Approach** (to find  $V_{GSQ}$  and  $I_{DQ}$ ):

- Calculate the value for

$$k = \frac{I_{D(on)}}{(V_{GS(on)} - V_{GS(Th)})^2}$$

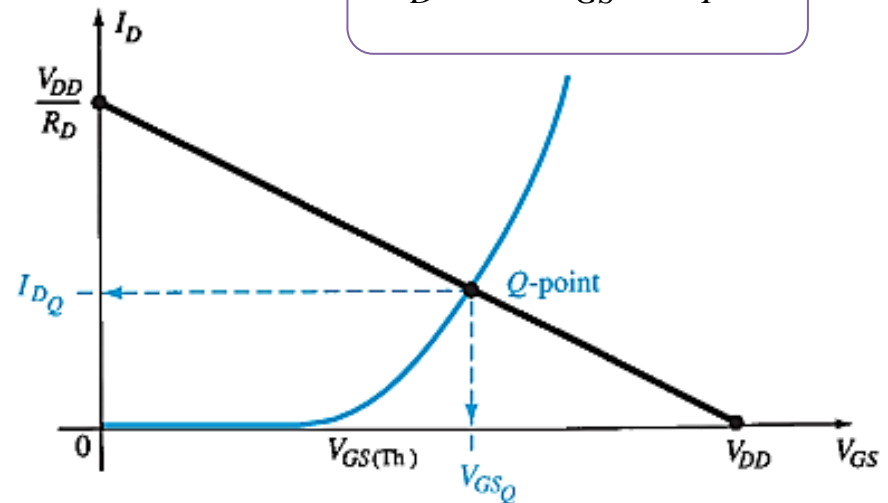
- Plot  $V_{GS}$  **vs**  $I_D$  for the range of interest.

- Plot :

$$V_{GS} = V_{DD} - I_D R_D$$

- Identify the Q-point.

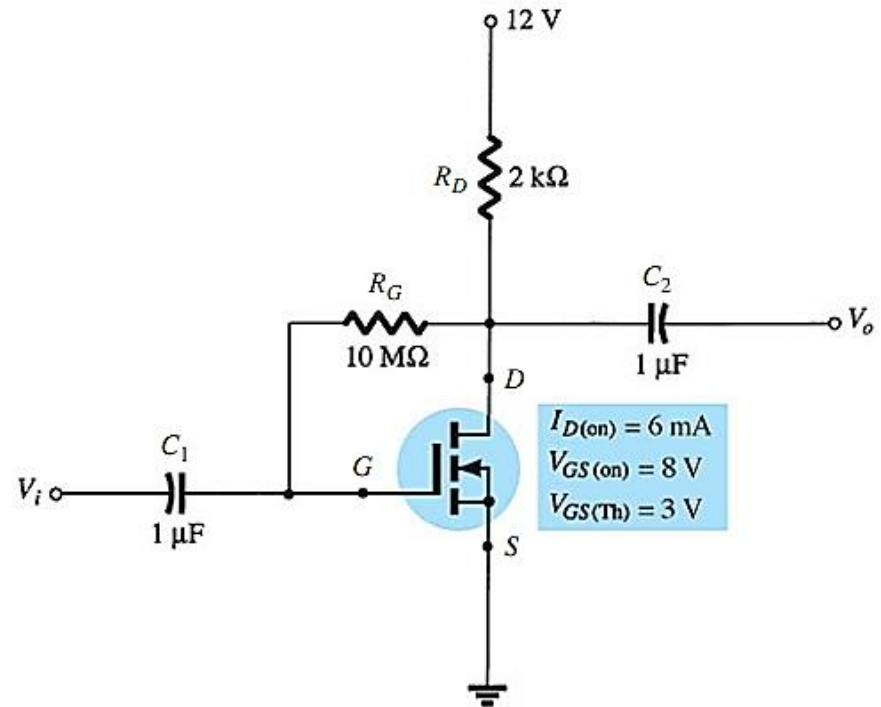
$$I_D = k(V_{GS} - V_T)^2$$



# E-MOSFET FEEDBACK BIAS EXAMPLE

- **Example 7.10:** Determine  $I_{DQ}$  and  $V_{DSQ}$  for the following circuit:

$$\begin{aligned}k &= \frac{I_{D(on)}}{(V_{GS(on)} - V_{GS(Th)})^2} \\&= \frac{6 \text{ mA}}{(8 \text{ V} - 3 \text{ V})^2} = \frac{6 \times 10^{-3}}{25} \text{ A/V}^2 \\&= 0.24 \times 10^{-3} \text{ A/V}^2\end{aligned}$$



**FIG. 7.40**

Example 7.10.



# E-MOSFET FEEDBACK BIAS EXAMPLE CONTD.

For  $V_{GS} = 6 \text{ V}$  (between 3 and 8 V):

$$\begin{aligned} I_D &= 0.24 \times 10^{-3} (6 \text{ V} - 3 \text{ V})^2 = 0.24 \times 10^{-3} (9) \\ &= 2.16 \text{ mA} \end{aligned}$$

as shown on Fig. 7.41. For  $V_{GS} = 10 \text{ V}$  (slightly greater than  $V_{GS(\text{Th})}$ ),

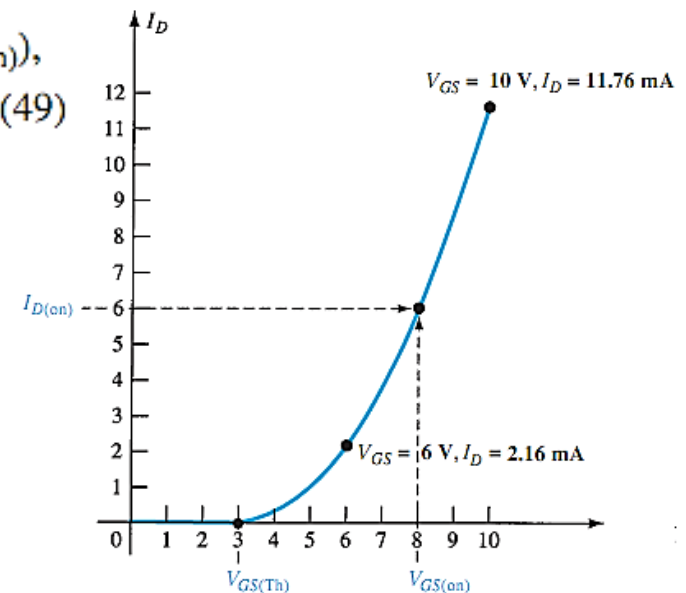
$$\begin{aligned} I_D &= 0.24 \times 10^{-3} (10 \text{ V} - 3 \text{ V})^2 = 0.24 \times 10^{-3} (49) \\ &= 11.76 \text{ mA} \end{aligned}$$

## For the Network Bias Line

$$\begin{aligned} V_{GS} &= V_{DD} - I_D R_D \\ &= 12 \text{ V} - I_D (2 \text{ k}\Omega) \end{aligned}$$

$$\text{Eq. (7.37): } V_{GS} = V_{DD} = 12 \text{ V} \big|_{I_D=0 \text{ mA}}$$

$$\text{Eq. (7.38): } I_D = \frac{V_{DD}}{R_D} = \frac{12 \text{ V}}{2 \text{ k}\Omega} = 6 \text{ mA} \big|_{V_{GS}=0 \text{ V}}$$



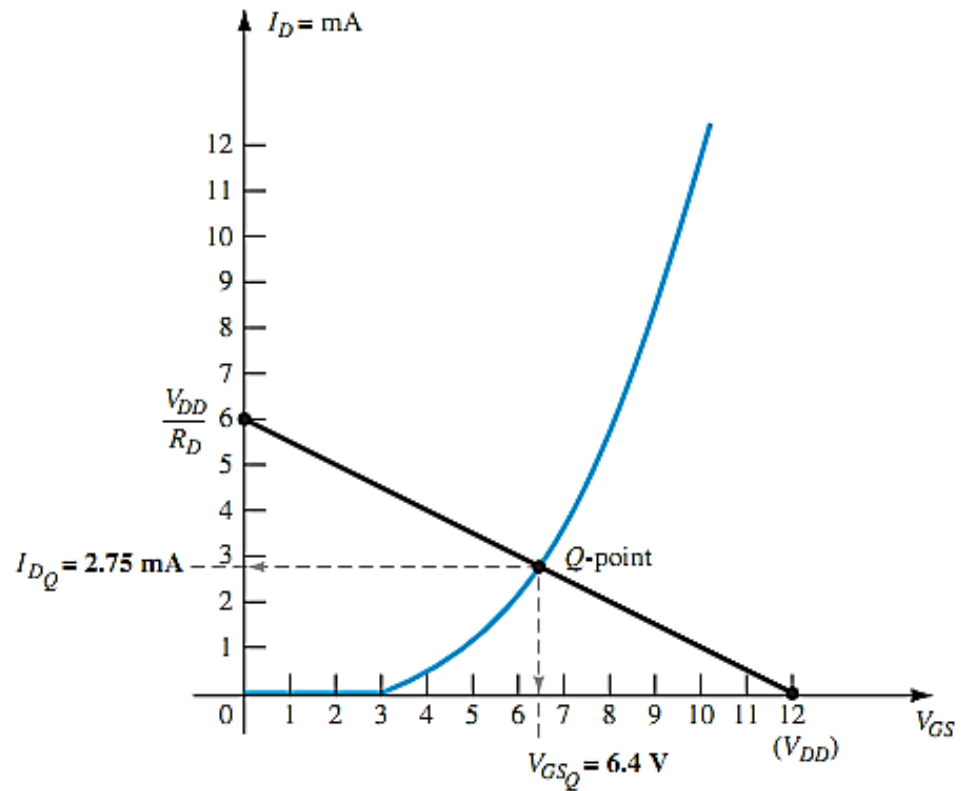
**FIG. 7.41**

Plotting the transfer curve for the MOSFET of Fig. 7.40.



## E-MOSFET FEEDBACK BIAS EXAMPLE CONTD.

$$\begin{aligned}I_{DQ} &= 2.75 \text{ mA} \\V_{GSQ} &= 6.4 \text{ V} \\V_{DSQ} &= V_{GSQ} = 6.4 \text{ V}\end{aligned}$$



**FIG. 7.42**

*Determining the Q-point for the network of Fig. 7.40.*



## p-CHANNEL FETs

- For **p-channel FETs** the **same** calculations and graphs are used, **except** that the **voltage polarities** and **current directions** are the **opposite**.
- The graphs will be mirrors of the n-channel graphs.



# End of Lecture-8

